



NPN AVALANCHE TRANSISTOR IN SOT23

Features

- Avalanche Transistor
- 50A Peak Avalanche Current (Pulse width = 20ns)
- BV_{CES} > 150V
- BV_{CEO} > 50V
- Specifically designed for Avalanche mode operation
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description

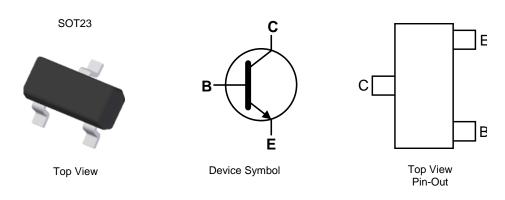
The FMMT413 is an NPN silicon planar bipolar transistor designed for operating in avalanche mode. Tight process control and low inductance packaging combine to produce high current pulses with fast edges.

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

Applications

- Laser Diode Drivers for Ranging and Measurement (LIDAR)
- Radar Systems
- Fast Edge Switch Generator
- High Speed Pulse Generators



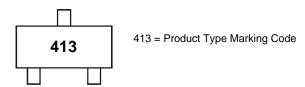
Ordering Information (Note 4)

Ī	Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	FMMT413TD	AEC-Q101	413	7	8	500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CES}	150	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	100	mA
Peak Collector Current (Pulse Width = 20ns)	I _{CM}	50	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	P _D	500	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead	(Note 6)	$R_{ heta JL}$	197	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

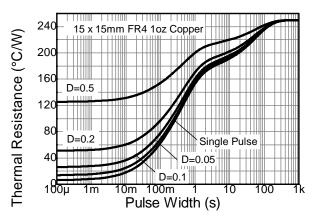
Notes:

^{5.} For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

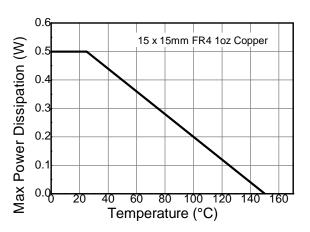
Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



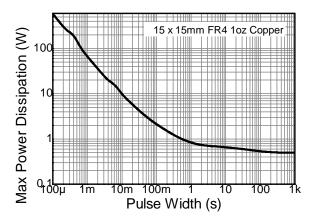
Thermal Characteristics and Derating Information



Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

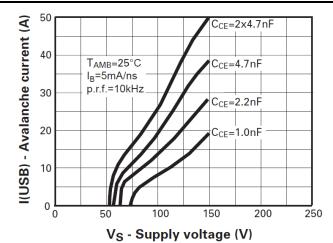
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CES}	150	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	50	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 120V
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 4V
Static Forward Current Transfer Ratio (Note 8)	h _{FE}	50	_	_	_	I _C = 10mA, V _{CE} = 10V
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	_	_	150	mV	$I_C = 10$ mA, $I_B = 1$ mA
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	_	_	800	mV	I _C = 10mA, I _B = 1mA
Pulsed Current in Second Breakdown (Note 9)		_	22	_	Α	V _C = 110V, C _{CE} = 4.7nF
Pulsed Current in Second Breakdown (Note 9)	I _{USB}	_	30	1	Α	$V_C = 130V, C_{CE} = 4.7nF$
Collector-Emitter Inductance	L _{ce}	_	2.5	_	nΗ	Standard SOT23 leads
Output Capacitance	C _{obo}	_	2	_	pF	$V_{CB} = 10V$, $I_E = 0$ f = 1MHz
Transition Frequency	f _T	_	150	_	MHz	V _{CE} = 5V, I _C = 10mA, f = 20MHz

Notes:

^{8.} Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%. 9. Measured with a circuit possessing an approximate loop inductance of 12nH.

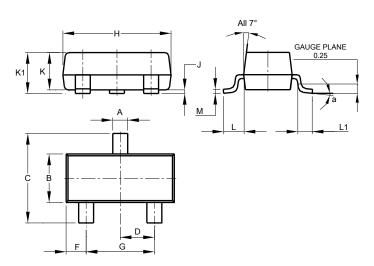


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



Package Outline Dimensions

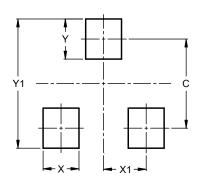
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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